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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

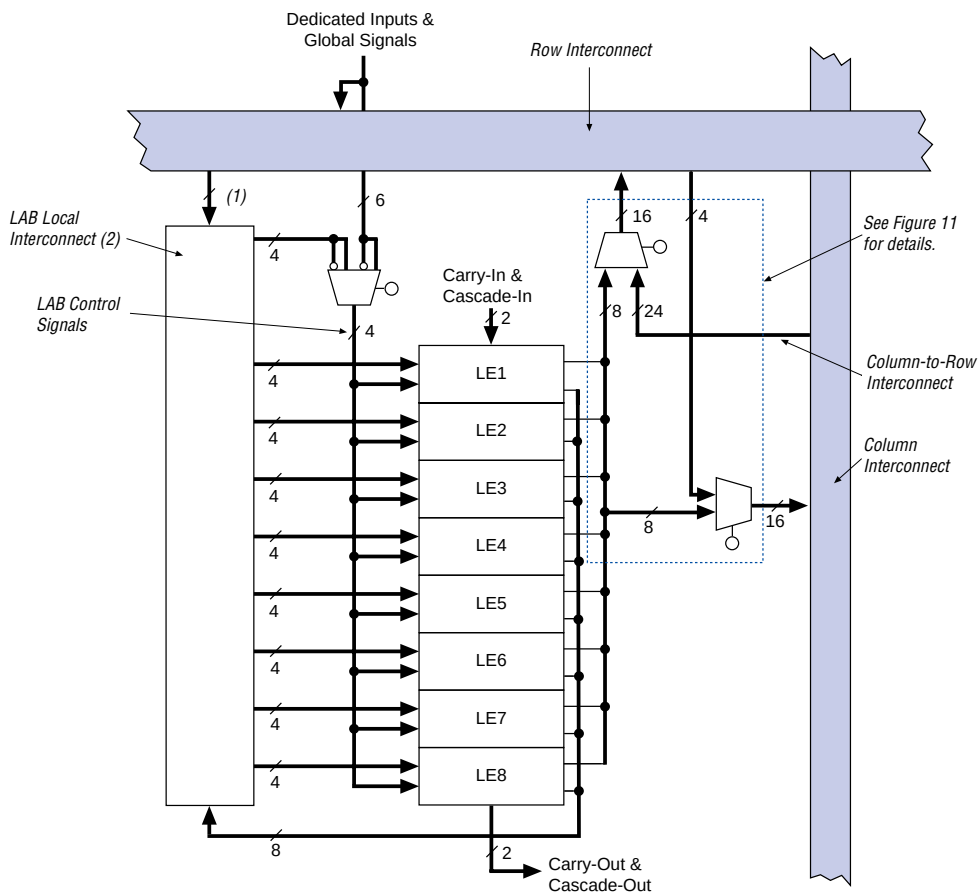
Details

Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	20480
Number of I/O	189
Number of Gates	116000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50vqc240-3n

Logic Array Block

Each LAB consists of eight LEs, their associated carry and cascade chains, LAB control signals, and the LAB local interconnect. The LAB provides the coarse-grained structure to the FLEX 10K architecture, facilitating efficient routing with optimum device utilization and high performance. See [Figure 5](#).

Figure 5. FLEX 10K LAB

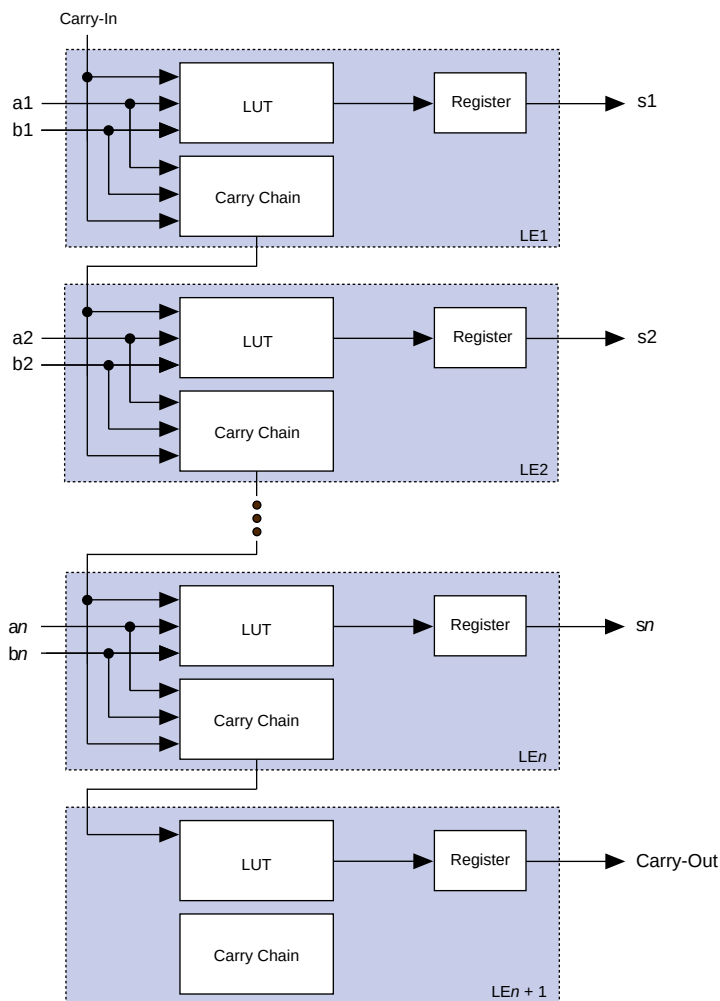


Notes:

- (1) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 22 inputs to the LAB local interconnect channel from the row; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 26.
- (2) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 30 LAB local interconnect channels; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 34 LABs.

Figure 7 shows how an n -bit full adder can be implemented in $n + 1$ LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can either be bypassed for simple adders or be used for an accumulator function. The carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next higher-order bit. The final carry-out signal is routed to an LE, where it can be used as a general-purpose signal.

Figure 7. Carry Chain Operation (n -bit Full Adder)



Up/Down Counter Mode

The up/down counter mode offers counter enable, clock enable, synchronous up/down control, and data loading options. These control signals are generated by the data inputs from the LAB local interconnect, the carry-in signal, and output feedback from the programmable register. The Up/down counter mode uses 2 three-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading. Data can also be loaded asynchronously with the clear and preset register control signals, without using the LUT resources.

Clearable Counter Mode

The clearable counter mode is similar to the up/down counter mode, but supports a synchronous clear instead of the up/down control. The clear function is substituted for the cascade-in signal in the up/down counter mode. Clearable counter mode uses 2 three-input LUTs: one generates the counter data, and the other generates the fast carry bit. Synchronous loading is provided by a 2-to-1 multiplexer. The output of this multiplexer is ANDed with a synchronous clear signal.

Internal Tri-State Emulation

Internal tri-state emulation provides internal tri-stating without the limitations of a physical tri-state bus. In a physical tri-state bus, the tri-state buffers' output enable (OE) signals select which signal drives the bus. However, if multiple OE signals are active, contending signals can be driven onto the bus. Conversely, if no OE signals are active, the bus will float. Internal tri-state emulation resolves contending tri-state buffers to a low value and floating buses to a high value, thereby eliminating these problems. The Altera software automatically implements tri-state bus functionality with a multiplexer.

Clear & Preset Logic Control

Logic for the programmable register's clear and preset functions is controlled by the DATA3, LABCTRL1, and LABCTRL2 inputs to the LE. The clear and preset control structure of the LE asynchronously loads signals into a register. Either LABCTRL1 or LABCTRL2 can control the asynchronous clear. Alternatively, the register can be set up so that LABCTRL1 implements an asynchronous load. The data to be loaded is driven to DATA3; when LABCTRL1 is asserted, DATA3 is loaded into the register.

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across devices; it provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, an LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal will reset all IOE registers, overriding any other control signals.

Tables 8 and 9 list the sources for each peripheral control signal, and the rows that can drive global signals. These tables also show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals.

Signals on the peripheral control bus can also drive the four global signals, referred to as GLOBAL0 through GLOBAL3 in [Tables 8 and 9](#). The internally generated signal can drive the global signal, providing the same low-skew, low-delay characteristics for an internally generated signal as for a signal driven by an input. This feature is ideal for internally generated clear or clock signals with high fan-out. When a global signal is driven by internal logic, the dedicated input pin that drives that global signal cannot be used. The dedicated input pin should be driven to a known logic state (such as ground) and not be allowed to float.

When the chip-wide output enable pin is held low, it will tri-state all pins on the device. This option can be set in the Global Project Device Options menu. Additionally, the registers in the IOE can be reset by holding the chip-wide reset pin low.

Row-to-IOE Connections

When an IOE is used as an input signal, it can drive two separate row channels. The signal is accessible by all LEs within that row. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the row channels. Up to eight IOEs connect to each side of each row channel. See [Figure 14](#).

Figure 14. FLEX 10K Row-to-IOE Connections

The values for m and n are provided in Table 10.

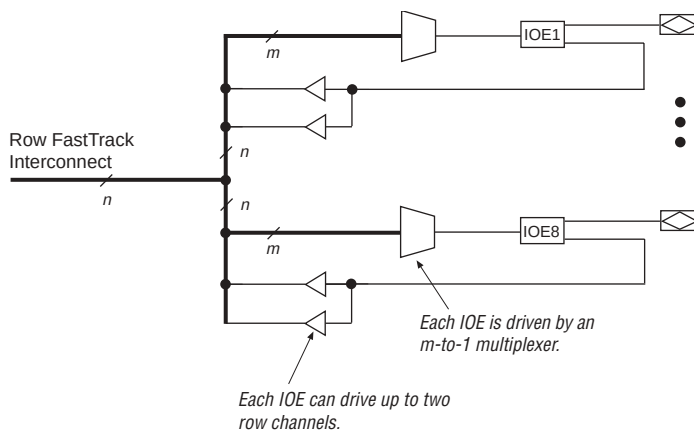


Table 12 describes the FLEX 10K device supply voltages and MultiVolt I/O support levels.

Table 12. Supply Voltages & MultiVolt I/O Support Levels

Devices	Supply Voltage (V)		MultiVolt I/O Support Levels (V)	
	V _{CCINT}	V _{CCIO}	Input	Output
FLEX 10K (1)	5.0	5.0	3.3 or 5.0	5.0
	5.0	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K50V (1)	3.3	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K130V	3.3	3.3	3.3 or 5.0	3.3 or 5.0
FLEX 10KA (1)	3.3	3.3	2.5, 3.3, or 5.0	3.3 or 5.0
	3.3	2.5	2.5, 3.3, or 5.0	2.5

Note

(1) 240-pin QFP packages do not support the MultiVolt I/O features, so they do not have separate V_{CCIO} pins.

Power Sequencing & Hot-Socketing

Because FLEX 10K devices can be used in a multi-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The V_{CCIO} and V_{CCINT} power supplies can be powered in any order.

Signals can be driven into FLEX 10KA devices before and during power up without damaging the device. Additionally, FLEX 10KA devices do not drive out during power up. Once operating conditions are reached, FLEX 10KA devices operate as specified by the user.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10K devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. All FLEX 10K devices can also be configured using the JTAG pins through the BitBlaster serial download cable, or ByteBlasterMV parallel port download cable, or via hardware that uses the Jam™ programming and test language. JTAG BST can be performed before or after configuration, but not during configuration. FLEX 10K devices support the JTAG instructions shown in Table 13.

Table 15. 32-Bit FLEX 10K Device IDCODE *Note (1)*

Device	IDCODE (32 Bits)			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer's Identity (11 Bits)	1 (1 Bit) (2)
EPF10K10, EPF10K10A	0000	0001 0000 0001 0000	00001101110	1
EPF10K20	0000	0001 0000 0010 0000	00001101110	1
EPF10K30, EPF10K30A	0000	0001 0000 0011 0000	00001101110	1
EPF10K40	0000	0001 0000 0100 0000	00001101110	1
EPF10K50, EPF10K50V	0000	0001 0000 0101 0000	00001101110	1
EPF10K70	0000	0001 0000 0111 0000	00001101110	1
EPF10K100, EPF10K100A	0000	0000 0001 0000 0000	00001101110	1
EPF10K130V	0000	0000 0001 0011 0000	00001101110	1
EPF10K250A	0000	0000 0010 0101 0000	00001101110	1

Notes:

- (1) The most significant bit (MSB) is on the left.
 (2) The least significant bit (LSB) for all JTAG IDCODEs is 1.

FLEX 10K devices include weak pull-ups on JTAG pins.



For more information, see the following documents:

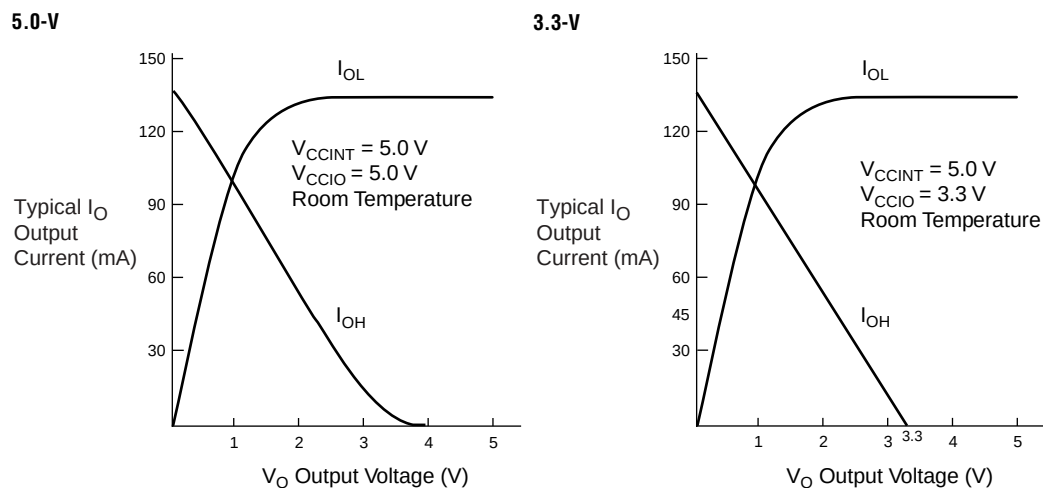
- *Application Note 39 (IEEE 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *Jam Programming & Test Language Specification*

Notes to tables:

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) Minimum DC input voltage is -0.5 V. During transitions, the inputs may undershoot to -2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
- (3) Numbers in parentheses are for industrial-temperature-range devices.
- (4) Maximum V_{CC} rise time is 100 ms. V_{CC} must rise monotonically.
- (5) Typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0$ V.
- (6) These values are specified under the Recommended Operation Condition shown in Table 18 on page 45.
- (7) The I_{OH} parameter refers to high-level TTL or CMOS output current.
- (8) The I_{OL} parameter refers to low-level TTL or CMOS output current. This parameter applies to open-drain pins as well as output pins.
- (9) This value is specified for normal device operation. The value may vary during power-up.
- (10) Capacitance is sample-tested only.

Figure 20 shows the typical output drive characteristics of FLEX 10K devices with 5.0-V and 3.3-V V_{CCIO} . The output driver is compliant with the 5.0-V *PCI Local Bus Specification, Revision 2.2* (for 5.0-V V_{CCIO}).

Figure 20. Output Drive Characteristics of FLEX 10K Devices



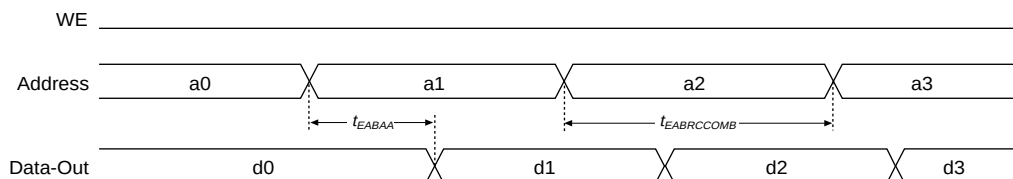
Notes to tables:

- (1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.
- (2) Operating conditions: $V_{CCIO} = 5.0 \text{ V} \pm 5\%$ for commercial use in FLEX 10K devices.
 $V_{CCIO} = 5.0 \text{ V} \pm 10\%$ for industrial use in FLEX 10K devices.
 $V_{CCIO} = 3.3 \text{ V} \pm 10\%$ for commercial or industrial use in FLEX 10KA devices.
- (3) Operating conditions: $V_{CCIO} = 3.3 \text{ V} \pm 10\%$ for commercial or industrial use in FLEX 10K devices.
 $V_{CCIO} = 2.5 \text{ V} \pm 0.2 \text{ V}$ for commercial or industrial use in FLEX 10KA devices.
- (4) Operating conditions: $V_{CCIO} = 2.5 \text{ V}, 3.3 \text{ V}, \text{ or } 5.0 \text{ V}$.
- (5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.
- (6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.
- (7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.
- (8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.
- (9) Contact Altera Applications for test circuit specifications and test conditions.
- (10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34.

Figure 29. EAB Asynchronous Timing Waveforms

EAB Asynchronous Read



EAB Asynchronous Write

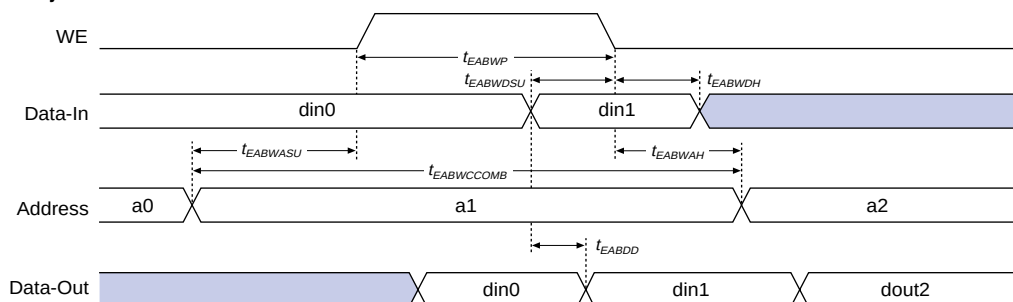


Table 42. EPF10K10 & EPF10K20 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATA CO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Table 45. EPF10K10 & EPF10K20 Device External Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{DDR}		16.1		20.0	ns
t_{INSU} (2), (3)	5.5		6.0		ns
t_{INH} (3)	0.0		0.0		ns
t_{OUTCO} (3)	2.0	6.7	2.0	8.4	ns

Table 46. EPF10K10 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	4.5		5.6		ns
t_{INHBIDIR}	0.0		0.0		ns
$t_{\text{OUTCOBIDIR}}$	2.0	6.7	2.0	8.4	ns
t_{XZBIDIR}		10.5		13.4	ns
t_{ZXBIDIR}		10.5		13.4	ns

Table 47. EPF10K20 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	4.6		5.7		ns
t_{INHBIDIR}	0.0		0.0		ns
$t_{\text{OUTCOBIDIR}}$	2.0	6.7	2.0	8.4	ns
t_{XZBIDIR}		10.5		13.4	ns
t_{ZXBIDIR}		10.5		13.4	ns

Notes to tables:

- (1) All timing parameters are described in Tables 32 through 38 in this data sheet.
- (2) Using an LE to register the signal may provide a lower setup time.
- (3) This parameter is specified by characterization.

Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters*Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATA CO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Table 66. EPF10K100 Device EAB Internal Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.5		1.9	ns
$t_{EABDATA2}$		4.8		4.8		6.0	ns
t_{EABWE1}		1.0		1.0		1.2	ns
t_{EABWE2}		5.0		5.0		6.2	ns
t_{EABCLK}		1.0		1.0		2.2	ns
t_{EABCO}		0.5		0.5		0.6	ns
$t_{EABYPASS}$		1.5		1.5		1.9	ns
t_{EABSU}	1.5		1.5		1.8		ns
t_{EABH}	2.0		2.0		2.5		ns
t_{AA}		8.7		8.7		10.7	ns
t_{WP}	5.8		5.8		7.2		ns
t_{WDSU}	1.6		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.5		0.5		0.6		ns
t_{WAH}	1.0		1.0		1.2		ns
t_{WO}		5.0		5.0		6.2	ns
t_{DD}		5.0		5.0		6.2	ns
t_{EABOUT}		0.5		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.8		5.8		7.2		ns

Table 68. EPF10K100 Device Interconnect Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		10.3		10.3		12.2	ns
t_{DIN2LE}		4.8		4.8		6.0	ns
$t_{DIN2DATA}$		7.3		7.3		11.0	ns
$t_{DCLK2IOE}$ without ClockLock or ClockBoost circuitry		6.2		6.2		7.7	ns
$t_{DCLK2IOE}$ with ClockLock or ClockBoost circuitry		2.3		–		–	ns
$t_{DCLK2LE}$ without ClockLock or ClockBoost circuitry		4.8		4.8		6.0	ns
$t_{DCLK2LE}$ with ClockLock or ClockBoost circuitry		2.3		–		–	ns
$t_{SAMELAB}$		0.4		0.4		0.5	ns
$t_{SAMEROW}$		4.9		4.9		5.5	ns
$t_{SAMECOLUMN}$		5.1		5.1		5.4	ns
$t_{DIFFROW}$		10.0		10.0		10.9	ns
$t_{TWOROWS}$		14.9		14.9		16.4	ns
$t_{LEPERIPH}$		6.9		6.9		8.1	ns
$t_{LABCARRY}$		0.9		0.9		1.1	ns
$t_{LABCASC}$		3.0		3.0		3.2	ns

Table 74. EPF10K50V Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{EABAA}		9.5		13.6		16.5		20.8	ns
$t_{EABRCCOMB}$	9.5		13.6		16.5		20.8		ns
$t_{EABRCREG}$	6.1		8.8		10.8		13.4		ns
t_{EABWP}	6.0		4.9		6.0		7.4		ns
$t_{EABWCCOMB}$	6.2		6.1		7.5		9.2		ns
$t_{EABWCREG}$	12.0		11.6		14.2		17.4		ns
t_{EABDD}		6.8		9.7		11.8		14.9	ns
$t_{EABDATACO}$		1.0		1.4		1.8		2.2	ns
$t_{EABDATASU}$	5.3		4.6		5.6		6.9		ns
$t_{EABDATAH}$	0.0		0.0		0.0		0.0		ns
$t_{EABWESU}$	4.4		4.8		5.8		7.2		ns
t_{EABWEH}	0.0		0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.8		1.1		1.4		2.1		ns
t_{EABWDH}	0.0		0.0		0.0		0.0		ns
$t_{EABWASU}$	4.5		4.6		5.6		7.4		ns
t_{EABWAH}	0.0		0.0		0.0		0.0		ns
t_{EABWO}		5.1		9.4		11.4		14.0	ns

Table 79. EPF10K130V Device IOE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.3		1.6		2.0	ns
t_{IOC}		0.4		0.5		0.7	ns
t_{IOCO}		0.3		0.4		0.5	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	2.6		3.3		3.8		ns
t_{IOH}	0.0		0.0		0.0		ns
t_{IOCLR}		1.7		2.2		2.7	ns
t_{OD1}		3.5		4.4		5.0	ns
t_{OD2}		—		—		—	ns
t_{OD3}		8.2		8.1		9.7	ns
t_{XZ}		4.9		6.3		7.4	ns
t_{ZX1}		4.9		6.3		7.4	ns
t_{ZX2}		—		—		—	ns
t_{ZX3}		9.6		10.0		12.1	ns
t_{INREG}		7.9		10.0		12.6	ns
t_{IOFD}		6.2		7.9		9.9	ns
t_{INCOMB}		6.2		7.9		9.9	ns

Table 94. EPF10K30A Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		5.5		6.5		8.5	ns
$t_{EABDATA2}$		1.1		1.3		1.8	ns
t_{EABWE1}		2.4		2.8		3.7	ns
t_{EABWE2}		2.1		2.5		3.2	ns
t_{EABCLK}		0.0		0.0		0.2	ns
t_{EABCO}		1.7		2.0		2.6	ns
$t_{EABYPASS}$		0.0		0.0		0.3	ns
t_{EABSU}	1.2		1.4		1.9		ns
t_{EABH}	0.1		0.1		0.3		ns
t_{AA}		4.2		5.0		6.5	ns
t_{WP}	3.8		4.5		5.9		ns
t_{WDSU}	0.1		0.1		0.2		ns
t_{WDH}	0.1		0.1		0.2		ns
t_{WASU}	0.1		0.1		0.2		ns
t_{WAH}	0.1		0.1		0.2		ns
t_{WO}		3.7		4.4		6.4	ns
t_{DD}		3.7		4.4		6.4	ns
t_{EABOUT}		0.0		0.1		0.6	ns
t_{EABCH}	3.0		3.5		4.0		ns
t_{EABCL}	3.8		4.5		5.9		ns

Notes to tables:

- (1) All timing parameters are described in Tables 32 through 38 in this data sheet.
- (2) Using an LE to register the signal may provide a lower setup time.
- (3) This parameter is specified by characterization.

Tables 106 through 112 show EPF10K250A device internal and external timing parameters.

Table 106. EPF10K250A Device LE Timing Microparameters <i>Note (1)</i>							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.4	ns
t_{CLUT}		1.2		1.3		1.6	ns
t_{RLUT}		2.0		2.3		2.7	ns
t_{PACKED}		0.4		0.4		0.5	ns
t_{EN}		1.4		1.6		1.9	ns
t_{CICO}		0.2		0.3		0.3	ns
t_{CGEN}		0.4		0.6		0.6	ns
t_{CGENR}		0.8		1.0		1.1	ns
t_{CASC}		0.7		0.8		1.0	ns
t_C		1.2		1.3		1.6	ns
t_{CO}		0.6		0.7		0.9	ns
t_{COMB}		0.5		0.6		0.7	ns
t_{SU}	1.2		1.4		1.7		ns
t_H	1.2		1.3		1.6		ns
t_{PRE}		0.7		0.8		0.9	ns
t_{CLR}		0.7		0.8		0.9	ns
t_{CH}	2.5		3.0		3.5		ns
t_{CL}	2.5		3.0		3.5		ns

- f_{MAX} = Maximum operating frequency in MHz
 N = Total number of logic cells used in the device
 tog_{LC} = Average percent of logic cells toggling at each clock (typically 12.5%)
 K = Constant, shown in [Tables 114 and 115](#)

Table 114. FLEX 10K K Constant Values

Device	K Value
EPF10K10	82
EPF10K20	89
EPF10K30	88
EPF10K40	92
EPF10K50	95
EPF10K70	85
EPF10K100	88

Table 115. FLEX 10KA K Constant Values

Device	K Value
EPF10K10A	17
EPF10K30A	17
EPF10K50V	19
EPF10K100A	19
EPF10K130V	22
EPF10K250A	23

This calculation provides an I_{CC} estimate based on typical conditions with no output load. The actual I_{CC} should be verified during operation because this measurement is sensitive to the actual pattern in the device and the environmental operating conditions.

To better reflect actual designs, the power model (and the constant K in the power calculation equations) for continuous interconnect FLEX devices assumes that logic cells drive FastTrack Interconnect channels. In contrast, the power model of segmented FPGAs assumes that all logic cells drive only one short interconnect segment. This assumption may lead to inaccurate results, compared to measured power consumption for an actual design in a segmented interconnect FPGA.

[Figure 32](#) shows the relationship between the current and operating frequency of FLEX 10K devices.

Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 1 of 3)

